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Schottky Barrier Rectifier

MBR30170MFS

This Schottky rectifier is high performance device in SO-8 FL package. The lower forward voltage, less leakage current, and small junction capacitance are suitable to high switching frequency high density DC to DC conversion application. Offering higher avalanche energy capability for Oring or reverse protection application. The SO-8 FL package provides an excellent thermal performance, less land area of board space, and low profile.

Features

- Lower Forward Voltage Drop
- Less Leakage Current in High Temperature
- Small Junction Capacitance for High Switching Frequency
- Higher Avalanche Energy Capability
- 175°C Operating Junction Temperature
- Good Alternative Solution of SMC and DPAK Package
- Small Footprint Land Area: 31.2 mm²
- Low Profile Maximum Height of 1.1 mm
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Mechanical Characteristics:

- Case: Molded Epoxy
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight: 95 mg (Approximately)
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Maximum for 10 Seconds
- MSL 1

Applications

- High Switching Frequency DC/DC Converter
- 2nd Rectifier
- Freewheeling Diode used with Inductive Load
- Oring / Reverse Protection



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SCHOTTKY BARRIER RECTIFIERS 30 AMPERES 170 VOLTS







B30170 = Specific Device Code A = Assembly Location

/ = Year

W = Work Week

ZZ = Lot Traceability

ORDERING INFORMATION

Device	Package	Shipping†
MBR30170MFST1G	SO-8 FL (Pb-Free)	1500 / Tape & Reel
MBR30170MFST3G	SO-8 FL (Pb-Free)	5000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

MAXIMUM RATINGS

R	ating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V _{RRM} V _{RWM} V _R	170	V
Continuous Forward Current (T _C = 162°	C, DC)	I _{F(DC)}	30	Α
Peak Repetitive Forward Current (T _C =	159°C, Square Wave, Duty = 0.5)	I _{FRM}	60	Α
Non-Repetitive Peak Surge Current	Current Sinusoidal Halfwave, 8.3 ms I _{FSM}	540	Α	
	Square wave, 1 ms		700	
	Square wave, 100 μs		1200	
Non-Repetitive Avalanche Energy (T _J =	25°C)	E _{AS}	280	mJ
Storage Temperature Range		T _{stg}	-65 to +175	°C
Operating Junction Temperature Range	(Note 1)	TJ	-55 to +175	°C
ESD Rating (Human Body Model)			3B	
ESD Rating (Machine Model)			M4	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ hetaJA}$	55	°C/W
Thermal Resistance, Junction-to-Case Bottom (Note 2)	$R_{ heta JCB}$	0.65	°C/W
Thermal Characterization, Junction-to-Case Top (Note 2)	ΨЈСТ	3.5	°C/W
Thermal Characterization, Junction-to-Lead of Cathode (Note 2)	ΨJLC	1.4	°C/W

^{2.} Assume 600 mm², 1 oz. copper bond pad on a FR4 board.

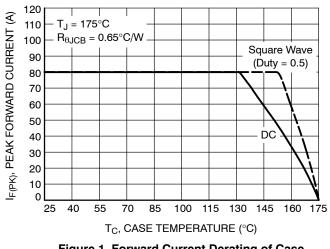
ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Тур	Max	Unit
Instantaneous Forward Voltage	V _F			V
$(I_F = 15 \text{ A}, T_J = 25^{\circ}\text{C})$		0.76	-	
$(I_F = 15 \text{ A}, T_J = 125^{\circ}\text{C})$		0.62	_	
$(I_F = 30 \text{ A}, T_J = 25^{\circ}\text{C})$		0.81	0.89	
$(I_F = 30 \text{ A}, T_J = 125^{\circ}\text{C})$		0.68	0.74	
Instantaneous Reverse Current	I _R			
(V _R = Rated DC Voltage, T _J = 25°C)		0.5	50	μΑ
(V _R = Rated DC Voltage, T _J = 125°C)		1.0	10	mA
Junction Capacitance	СЈ			pF
$(V_R = 1 \text{ V}, T_J = 25^{\circ}\text{C}, f = 1 \text{ MHz})$		821	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 3. Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%.

^{1.} The heat generated must be less than the thermal conductivity from Junction-to-Ambient $dP_D/dT_J < 1/R_{\theta JA}$ The reliability may be affected by leakage current when device operates near to rated voltage and maximum junction temperature.

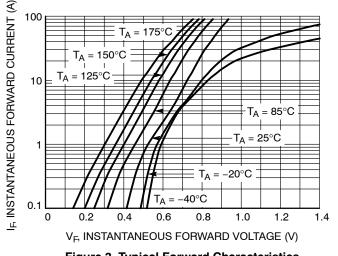
TYPICAL CHARACTERISTICS



 $I_{\mathsf{F}(\mathsf{PK})},$ PEAK FORWARD CURRENT (A) $T_{.1} = 175^{\circ}C$ $R_{\theta JA} = 55^{\circ}C/W$ 25 Square Wave D = 0.220 D = 0.315 D = 0.510 DC 5 25 40 85 100 115 160 175 TA, AMBIENT TEMPERATURE (°C)

Figure 1. Forward Current Derating of Case Temperature

Figure 2. Forward Current Derating of Ambient Temperature



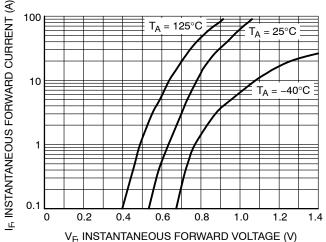
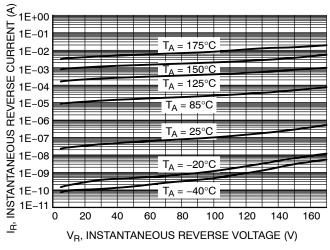


Figure 3. Typical Forward Characteristics

Figure 4. Maximum Forward Characteristics



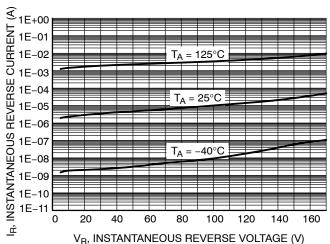


Figure 5. Typical Reverse Characteristics

Figure 6. Maximum Reverse Characteristics

TYPICAL CHARACTERISTICS

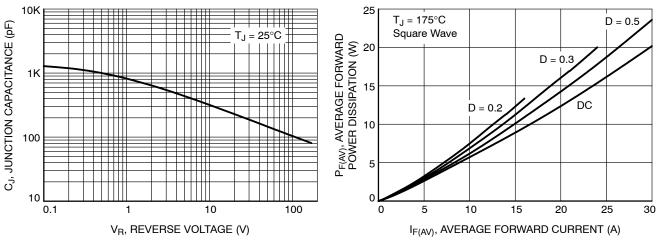


Figure 7. Typical Junction Capacitance

Figure 8. Average Forward Power Dissipation

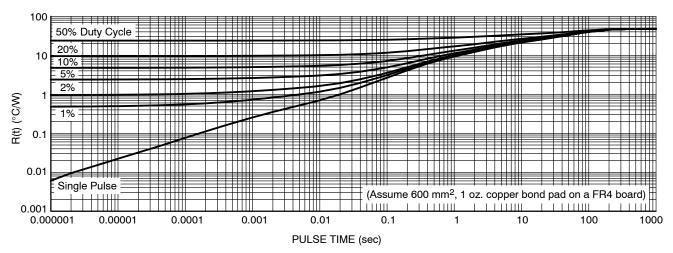
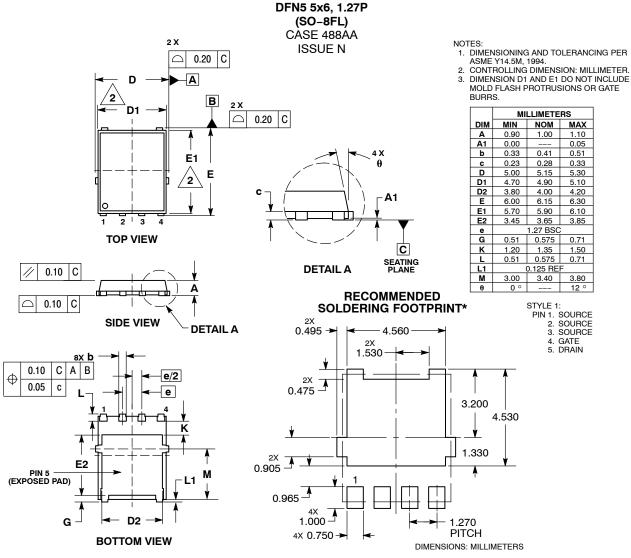


Figure 9. Typical Thermal Characteristics, Junction-to-Ambient

PACKAGE DIMENSIONS



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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